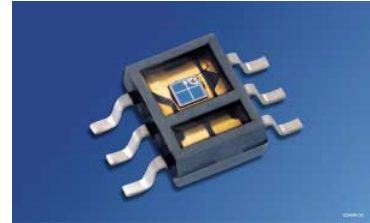


NPN-Silizium-Fototransistor im SMT-Gehäuse Silicon NPN Phototransistor in SMT Package

SFH 3201



Vorläufige Daten / Preliminary Data

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 460 nm bis 1080 nm
- Hohe Linearität
- SMT-Bauform ohne Basisanschluß, geeignet für Vapor Phase-Löten, IR-Reflow-Löten (JEDEC level 4) und Wellenlöten (JEDEC level 4)
- Nur gegurtet lieferbar

Anwendungen

- Umgebungslicht-Detektor
- Lichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 460 nm to 1080 nm
- High linearity
- SMT package without base connection, suitable for vapor phase, IR reflow soldering (JEDEC level 4) and wave soldering (JEDEC level 4)
- Available only on tape and reel

Applications

- Ambient light detector
- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
SFH 3201	Q62702-P5043	P-DSO-6
SFH 3201-2/3	Q62702-P5209	P-DSO-6

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Kollektor-Emitterspannung Collector-emitter voltage	V_{CE}	20	V
Kollektor-Emitterspannung, $t < 120$ s Collector-emitter voltage	V_{CE}	70	V
Kollektorstrom Collector current	I_C	50	mA
Kollektorspitzenstrom, $\tau < 10$ μ s Collector surge current	I_{CS}	100	mA
Emitter-Kollektorspannung Emitter-collector voltage	V_{EC}	7	V
Verlustleistung, $T_A = 25$ °C Total power dissipation	P_{tot}	120	mW
Wärmewiderstand für Montage auf PC-Board Thermal resistance for mounting on pcb	R_{thJA}	500	K/W

Kennwerte ($T_A = 25\text{ °C}$)

Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	460 ... 1080	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	0.55	mm ²
Abmessung der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	1 × 1	mm × mm
Halbwinkel Half angle	φ	± 60	Grad deg.
Kapazität, $V_{\text{CE}} = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_{CE}	15	pF
Dunkelstrom Dark current $V_{\text{CE}} = 20\text{ V}$, $E = 0$	I_{CEO}	3 (≤ 200)	nA

Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.

The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

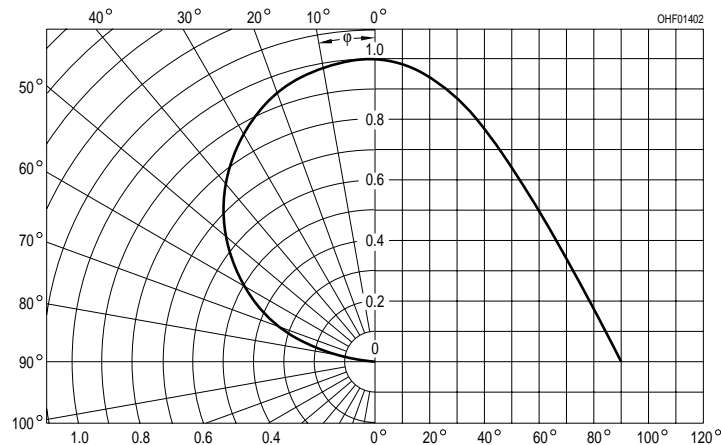
Bezeichnung Parameter	Symbol Symbol	Wert Value			Einheit Unit
		-1	-2	-3	
Fotostrom, $\lambda = 950 \text{ nm}$ Photocurrent $E_e = 0.1 \text{ mW/cm}^2$, $V_{CE} = 5 \text{ V}$ $E_v = 1000 \text{ lx}$, Normlicht/ standard light A, $V_{CE} = 5 \text{ V}$	I_{PCE}	63 ... 125	100 ... 200	160 ... 320	μA
	I_{PCE}	1.65	2.6	4.2	mA
Anstiegszeit/Abfallzeit Rise and fall time $I_C = 1 \text{ mA}$, $V_{CC} = 5 \text{ V}$, $R_L = 1 \text{ k}\Omega$	t_r , t_f	16	24	34	μs
Kollektor-Emitter- Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}^{1)} \times 0.3$, $E_e = 0.1 \text{ mW/cm}^2$	V_{CEsat}	170 (≤ 250)	170 (≤ 250)	170 (≤ 250)	mV

1) I_{PCEmin} ist der minimale Fotostrom der jeweiligen Gruppe.

1) I_{PCEmin} is the min. photocurrent of the specified group.

Directional Characteristics

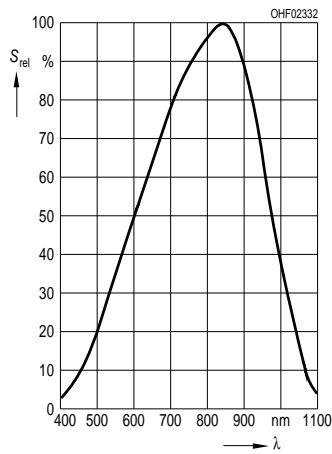
$$S_{rel} = f(\varphi)$$



$T_A = 25\text{ }^\circ\text{C}$, $\lambda = 950\text{ nm}$

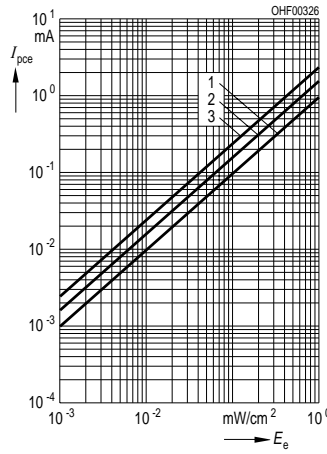
Rel. Spectral Sensitivity,

$S_{rel} = f(\lambda)$



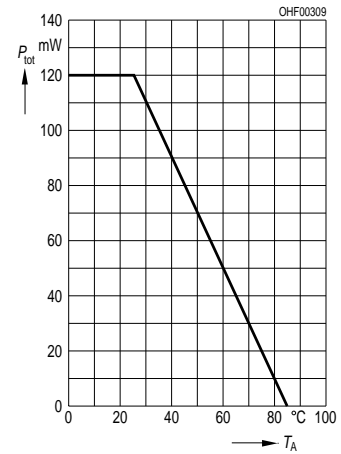
Photocurrent

$I_{PCE} = f(E_e), V_{CE} = 5\text{ V}$

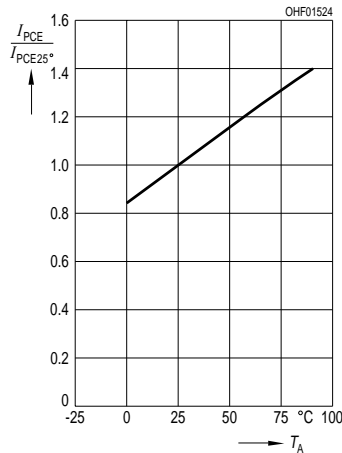


Total Power Dissipation

$P_{tot} = f(T_A)$

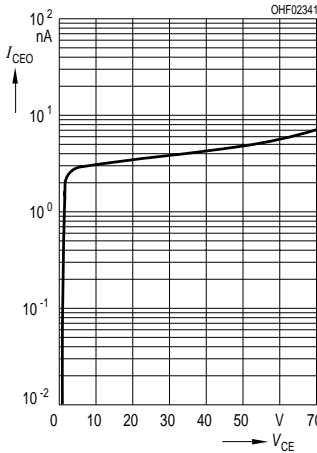


Photocurrent $I_{PCE} = f(T_A)$,
 $V_{CE} = 5\text{ V}$, normalized to $25\text{ }^\circ\text{C}$



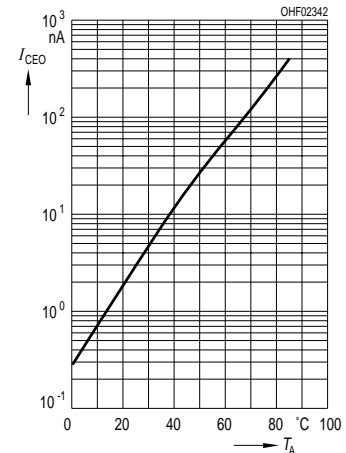
Dark Current

$I_{CEO} = f(V_{CE}), E = 0$



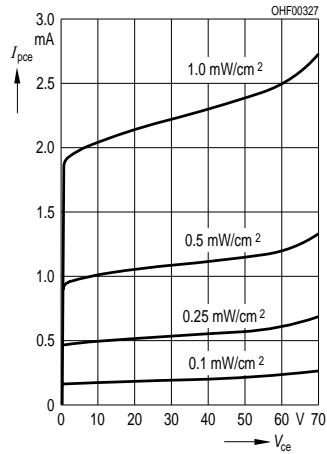
Dark Current

$I_{CEO} = f(T_A), V_{CE} = 10\text{ V}, E = 0$



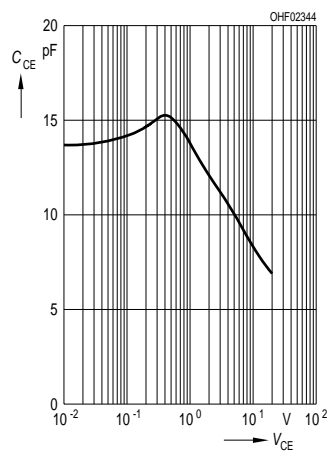
Photocurrent

$I_{PCE} = f(V_{CE})$

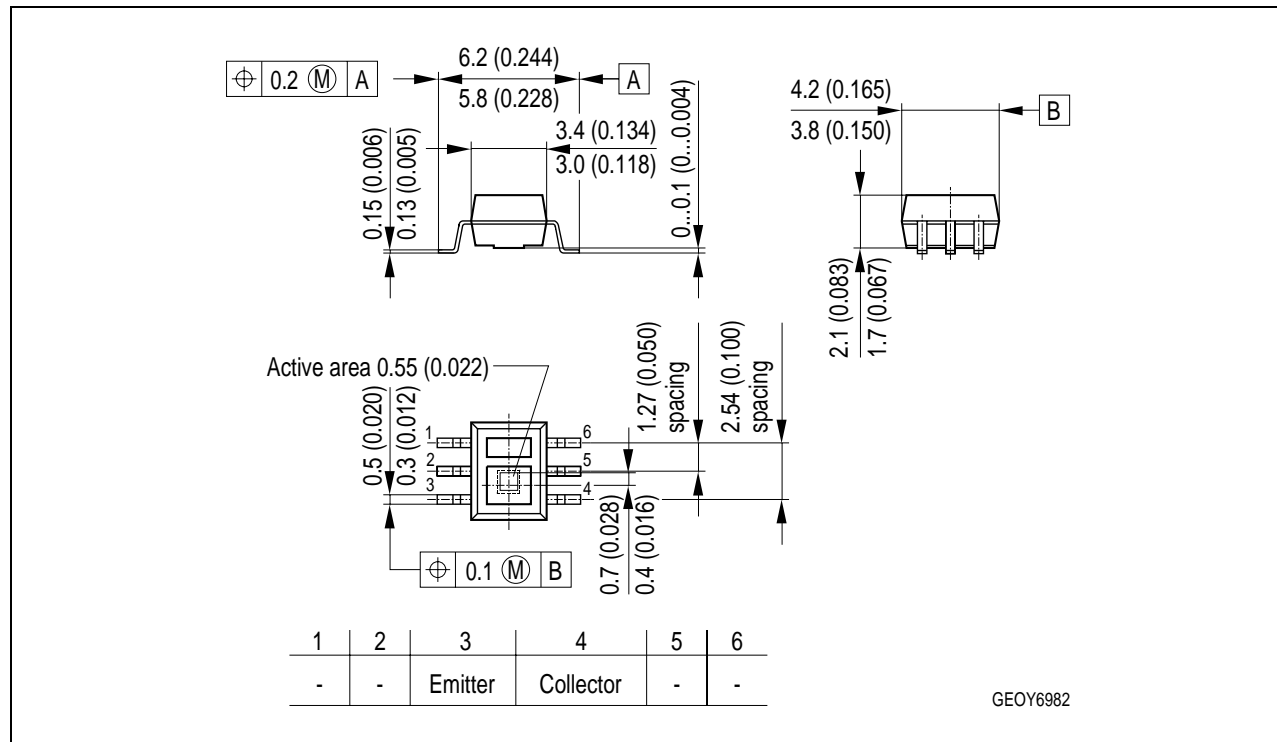


Collector-Emitter Capacitance

$C_{CE} = f(V_{CE}), f = 1\text{ MHz}$



Maßzeichnung
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Löthinweise
Soldering Conditions

Bauform Type	Drypack Level acc. to IPS-stand. 020	Tauch-, Schwalllötung Dip, Wave Soldering		Reflowlötung Reflow Soldering		Kolbenlötung Iron Soldering
		Peak Temp. (solderbath)	Max. Time in Peak Zone	Peak Temp. (package temp.)	Max. Time in Peak Zone	(Iron temp.)
SFH 3201	4	260	10 s	245 °C	10 s	n.a.

Bitte Verarbeitungshinweise für SMT-Bauelemente beachten!

Please observe the handling guidelines for SMT devices!

Published by OSRAM Opto Semiconductors GmbH & Co. OHG

Wernerwerkstrasse 2, D-93049 Regensburg

© All Rights Reserved.

Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances. For information on the types in question please contact our Sales Organization.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components ¹, may only be used in life-support devices or systems ² with the express written approval of OSRAM OS.

¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.